# **Analog Multiplexer/ Demultiplexer**

## **High-Performance Silicon-Gate CMOS**

The MC74LVX4051 utilizes silicon–gate CMOS technology to achieve fast propagation delays, low ON resistances, and low leakage currents. This analog multiplexer/demultiplexer controls analog voltages that may vary across the complete power supply range (from  $V_{CC}$  to  $V_{EE}). \label{eq:control}$ 

The LVX4051 is similar in pinout to the LVX8051, the HC4051A, and the metal—gate MC14051B. The Channel—Select inputs determine which one of the Analog Inputs/Outputs is to be connected, by means of an analog switch, to the Common Output/Input. When the Enable pin is HIGH, all analog switches are turned off.

The Channel–Select and Enable inputs are compatible with standard CMOS outputs. These inputs are overvoltage tolerant (OVT) for level translation from 6.0 V down to 3.0 V.

This device has been designed so the ON resistance ( $R_{ON}$ ) is more linear over input voltage than the  $R_{ON}$  of metal-gate CMOS analog switches and High-Speed CMOS analog switches.

#### **Features**

- Fast Switching and Propagation Speeds
- Low Crosstalk Between Switches
- Analog Power Supply Range  $(V_{CC} V_{EE}) = -3.0 \text{ V}$  to +3.0 V
- Digital (Control) Power Supply Range  $(V_{CC} GND) = 2.5$  to 6.0 V
- Improved Linearity and Lower ON Resistance Than Metal–Gate, HSL, or VHC Counterparts
- Low Noise
- Designed to Operate on a Single Supply with V<sub>EE</sub> = GND, or Using Split Supplies up to ±3.0 V
- Break-Before-Make Circuitry
- These Devices are Pb-Free and are RoHS Compliant



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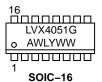


QFN16 MN SUFFIX CASE 485AW SOIC-16 D SUFFIX CASE 751B TSSOP-16 DT SUFFIX CASE 948F

#### **MARKING DIAGRAMS**



QFN16





TSSOP-16

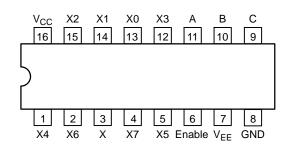
LVX4051 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week

G or ■ = Pb–Free Package
(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.



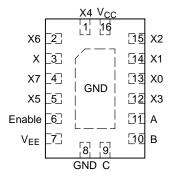


Figure 1. Pin Connection Diagrams (Top View)

## **FUNCTION TABLE**

Conti	rol Inp			
		Select	t	
Enable	С	В	Α	ON Channels
L	L	L	L	X0
L	L	L	Н	X1
L	L	Н	L	X2
L	L	Н	Н	X3
L	Н	L	L	X4
L	Н	L	Н	X5
L	Н	Н	L	X6
L	Н	Н	Н	X7
Н	Х	Χ	Χ	NONE
X = Don't Car	e			

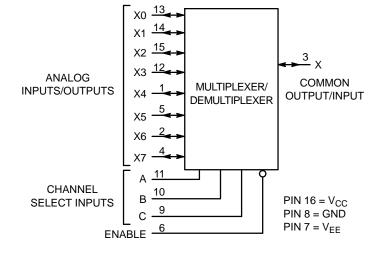


Figure 2. Logic Diagram
Single-Pole, 8-Position Plus Common Off

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LVX4051DG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74LVX4051DR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC74LVX4051DTG	TSSOP-16 (Pb-Free)	96 Units / Rail
MC74LVX4051DTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
MC74LVX4051MNTWG	QFN-16 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **MAXIMUM RATINGS**

Symbol	Parar	neter	Value	Unit
V <sub>EE</sub>	Negative DC Supply Voltage	(Referenced to GND)	-7.0 to +0.5	V
V <sub>CC</sub>	Positive DC Supply Voltage	(Referenced to GND) (Referenced to $V_{EE}$ )	0.5 to + 7.0 -0.5 to + 7.0	V
V <sub>IS</sub>	Analog Input Voltage		$V_{EE}$ -0.5 to $V_{CC}$ + 0.5	V
$V_{IN}$	Digital Input Voltage	(Referenced to GND)	-0.5 to 7.0	V
I	DC Current, Into or Out of Any Pin		±50	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 S	Seconds	260	°C
TJ	Junction Temperature under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance	SOIC TSSOP	143 164	°C/W
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35%	UL 94-V0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 200 > 1000	٧
I <sub>LATCHUP</sub>	Latchup Performance Ab	pove V <sub>CC</sub> and Below GND at 125°C (Note 4)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Tested to EIA/JESD22-A114-A.
- 2. Tested to EIA/JESD22-A115-A.
- 3. Tested to JESD22-C101-A.
- 4. Tested to EIA/JESD78.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Min	Max	Unit
V <sub>EE</sub>	Negative DC Supply Voltage	(Referenced to GND)	-6.0	GND	V
V <sub>CC</sub>	Positive DC Supply Voltage	(Referenced to GND) (Referenced to V <sub>EE</sub> )	2.5 2.5	6.0 6.0	V
V <sub>IS</sub>	Analog Input Voltage		V <sub>EE</sub>	V <sub>CC</sub>	V
$V_{IN}$	Digital Input Voltage	(Note 5) (Referenced to GND)	0	6.0	V
T <sub>A</sub>	Operating Temperature Range, All Package Types		-55	125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Channel Select or Enable Inputs)	$V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	100 20	ns/V

<sup>5.</sup> Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

## DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

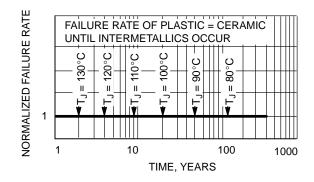


Figure 3. Failure Rate vs. Time Junction Temperature

## DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

			V <sub>CC</sub>	Guara	nit		
Symbol	Parameter	Condition	v	–55 to 25°C	≤85°C	≤125°C	Unit
V <sub>IH</sub>	Minimum High–Level Input Voltage, Channel–Select or Enable Inputs		2.5 3.0 4.5 6.0	1.90 2.10 3.15 4.2	1.90 2.10 3.15 4.2	1.90 2.10 3.15 4.2	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage, Channel-Select or Enable Inputs		2.5 3.0 4.5 6.0	0.6 0.9 1.35 1.8	0.6 0.9 1.35 1.8	0.6 0.9 1.35 1.8	V
I <sub>IN</sub>	Maximum Input Leakage Current, Channel–Select or Enable Inputs	V <sub>IN</sub> = 6.0 or GND	0 V to 6.0 V	±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	Channel Select, Enable and V <sub>IS</sub> = V <sub>CC</sub> or GND	6.0	4.0	40	80	μΑ

## DC ELECTRICAL CHARACTERISTICS - Analog Section

			V <sub>CC</sub>	V <sub>EE</sub>	Guara	nteed Lin	nit	
Symbol	Parameter	Test Conditions	V	V	–55 to 25°C	≤85°C	≤125°C	Unit
R <sub>ON</sub>	Maximum "ON" Resistance	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = \frac{1}{2} (V_{CC} - V_{EE})$ $ I_{S}  = 2.0 \text{ mA}$ (Figure 4)	3.0 4.5 3.0	0 0 -3.0	86 37 26	108 46 33	120 55 37	Ω
ΔR <sub>ON</sub>	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$\begin{aligned} V_{IN} &= V_{IL} \text{ or } V_{IH} \\ V_{IS} &= \frac{1}{2} \left( V_{CC} - V_{EE} \right) \\  I_{S}  &= 2.0 \text{ mA} \end{aligned}$	3.0 4.5 3.0	0 0 -3.0	15 13 10	20 18 15	20 18 15	Ω
l <sub>off</sub>	Maximum Off-Channel Leakage Current, Any One Channel	$V_{\text{in}} = V_{\text{IL}} \text{ or } V_{\text{IH}};$ $V_{\text{IO}} = V_{\text{CC}} \text{ or GND};$ Switch Off (Figure 3)	5.5 +3.0	0 -3.0	0.1 0.1	0.5 0.5	1.0 1.0	μΑ
	Maximum Off–Channel Leakage Current, Common Channel	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IO} = V_{CC} \text{ or GND};$ Switch Off (Figure 4)	5.5 +3.0	0 -3.0	0.2 0.2	2.0 2.0	4.0 4.0	
I <sub>on</sub>	Maximum On–Channel Leakage Current, Channel–to–Channel	$V_{in} = V_{IL} \text{ or } V_{IH};$ Switch-to-Switch = $V_{CC} \text{ or GND};$ (Figure 5)	5.5 +3.0	0 -3.0	0.2 0.2	2.0 2.0	4.0 4.0	μΑ

## **AC CHARACTERISTICS** (Input $t_r = t_f = 3 \text{ ns}$ )

						Guarai	nteed Lim	nit	
			V <sub>CC</sub>	V <sub>EE</sub>	–55 to	25°C			
Symbol	Parameter	Test Conditions	>	V	Min	Тур*	≤ <b>85</b> °C	≤125°C	Unit
t <sub>BBM</sub>	Minimum Break-Before-Make Time	$V_{IN} = V_{IL}$ or $V_{IH}$ $V_{IS} = V_{CC}$ $R_L = 300 \Omega$ , $C_L = 35 pF$ (Figures 12 and 13)	3.0 4.5 3.0	0.0 0.0 -3.0	1.0 1.0 1.0	6.5 5.0 3.5		1 1	ns

<sup>\*</sup>Typical Characteristics are at 25°C.

## AC CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 3 \text{ ns}$ )

		Guaranteed Limit									
		v <sub>cc</sub>	V <sub>EE</sub>	-	-55 to 25°	С	≤85	5°C	≤12	5°C	
Symbol	Parameter	V	V	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> ,	Maximum Propagation Delay,	2.5	0			40		45		50	ns
$t_{PHL}$	Channel–Select to Analog	3.0	0			28		30		35	
	Output	4.5	0			23		25		30	
	(Figures 16 and 17)	3.0	-3.0			23		25		28	
t <sub>PLZ</sub> ,	Maximum Propagation Delay,	2.5	0			40		45		50	ns
t <sub>PHZ</sub>	Enable to Analog Output (Fig-	3.0	0			28		30		35	
	ures 14 and 15)	4.5	0			23		25		30	
		3.0	-3.0			23		25		28	
t <sub>PZL</sub> ,	Maximum Propagation Delay,	2.5	0			40		45		50	ns
t <sub>PZH</sub>	Enable to Analog Output (Fig-	3.0	0			28		30		35	
	ures 14 and 15)	4.5	0			23		25		30	
		3.0	-3.0			23		25		28	

			Typical @ 25°C, V <sub>CC</sub> = 5.0 V, V <sub>EE</sub> = 0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Figure 18) (N	ote 6)	45	pF
C <sub>IN</sub>	Maximum Input Capacitance, Channel-Select	or Enable Inputs	10	pF
C <sub>I/O</sub>	Maximum Capacitance (All Switches Off)	Analog I/O Common O/I Feedthrough	10 10 1.0	pF

<sup>6.</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

## **ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)**

			v <sub>cc</sub>	V <sub>EE</sub>	Тур	
Symbol	Parameter	Condition	v	٧	25°C	Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response	V <sub>IS</sub> = ½ (V <sub>CC</sub> - V <sub>EE</sub> ) Ref and Test Attn = 10 dB Source Amplitude = 0 dB (Figure 7)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 -3.0	80 80 80 80	MHz
V <sub>ISO</sub>	Off-Channel Feedthrough Isolation	f = 1 MHz; $V_{IS} = \frac{1}{2} (V_{CC} - V_{EE})$ Adjust Network Analyzer output to 10 dBm on each output from the power splitter (Figures 8 and 9)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 -3.0	-70 -70 -70 -70	dB
V <sub>ONL</sub>	Maximum Feedthrough On Loss	V <sub>IS</sub> = ½ (V <sub>CC</sub> – V <sub>EE</sub> ) Adjust Network Analyzer output to 10 dBm on each output from the power splitter (Figure 11)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 -3.0	-2 -2 -2 -2	dB
Q	Charge Injection	$\begin{array}{l} V_{IN}=V_{CC} \text{ to } V_{EE,}  f_{IS}=1 \text{ kHz, } t_r=t_f=3 \text{ ns} \\ R_{IS}=0  \Omega,  C_L=1000 \text{ pF, } Q=C_L * \Delta V_{OUT} \\ \text{(Figure 10)} \end{array}$	5.0 3.0	0.0 -3.0	9.0 12	pC
THD	Total Harmonic Distortion THD + Noise	$\begin{split} f_{IS} &= 1 \text{ MHz, R}_L = 10 \text{ K}\Omega, C_L = 50 \text{ pF,} \\ V_{IS} &= 5.0 \text{ V}_{PP} \text{ sine wave} \\ V_{IS} &= 6.0 \text{ V}_{PP} \text{ sine wave} \\ \text{(Figure 19)} \end{split}$	6.0 3.0	0.0 -3.0	0.10 0.05	%

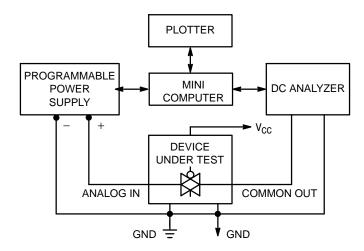
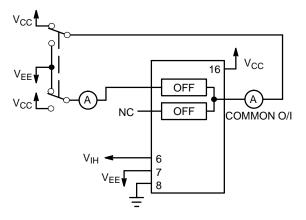


Figure 4. On Resistance, Test Set-Up



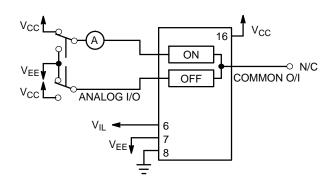


Figure 5. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

Figure 6. Maximum On Channel Leakage Current, Channel to Channel, Test Set-Up

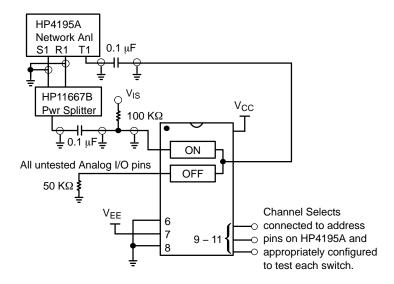


Figure 7. Maximum On Channel Bandwidth, Test Set-Up

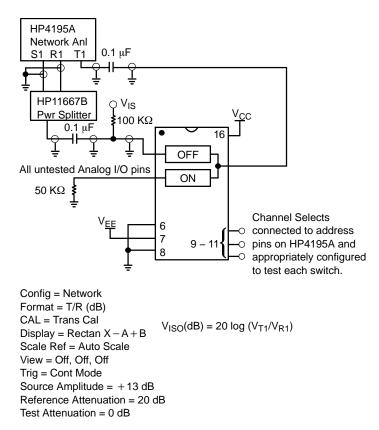


Figure 8. Maximum Off Channel Feedthrough Isolation, Test Set-Up

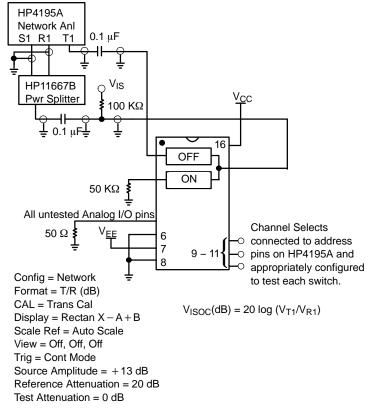
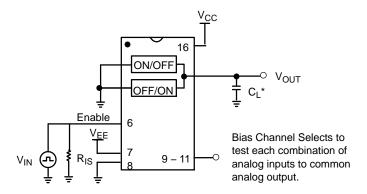


Figure 9. Maximum Common-Channel Feedthrough Isolation, Test Set-Up



\*Includes all probe and jig capacitance.

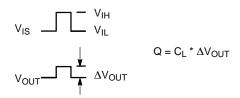


Figure 10. Charge Injection, Test Set-Up

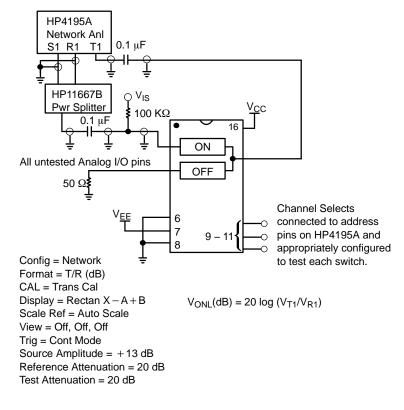


Figure 11. Maximum On Channel Feedthrough On Loss, Test Set-Up

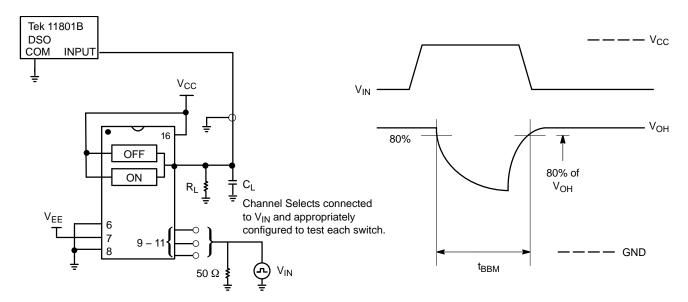


Figure 12. Break-Before-Make, Test Set-Up

Figure 13. Break-Before-Make Time

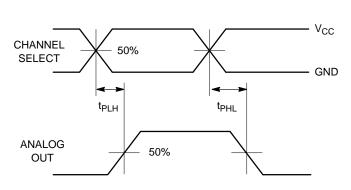
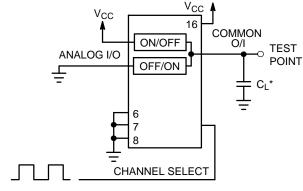


Figure 14. Propagation Delays, Channel Select to Analog Out



\*Includes all probe and jig capacitance.

Figure 15. Propagation Delay, Test Set-Up Channel Select to Analog Out

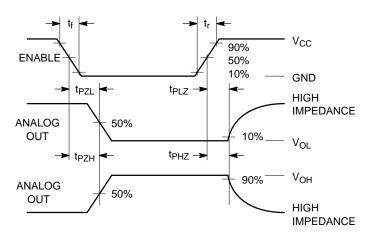


Figure 16. Propagation Delays, Enable to Analog Out

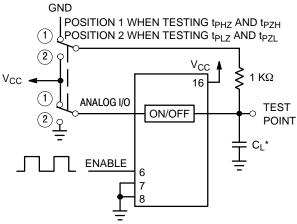


Figure 17. Propagation Delay, Test Set-Up Enable to Analog Out

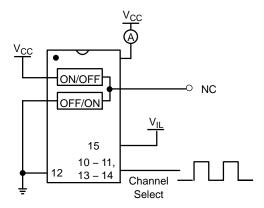


Figure 18. Power Dissipation Capacitance, Test Set-Up

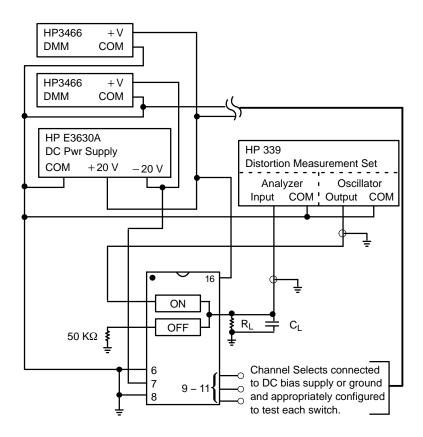


Figure 19. Total Harmonic Distortion, Test Set-Up

#### **APPLICATIONS INFORMATION**

The Channel Select and Enable control pins should be at  $V_{CC}$  or GND logic levels.  $V_{CC}$  being recognized as a logic high and GND being recognized as a logic low. In this example:

$$V_{CC} = +5 \text{ V} = \text{logic high}$$
  
 $GND = 0 \text{ V} = \text{logic low}$ 

The maximum analog voltage swing is determined by the supply voltages  $V_{CC}$  and  $V_{EE}$ . The positive peak analog voltage should not exceed  $V_{CC}$ . Similarly, the negative peak analog voltage should not go below  $V_{EE}$ . In this example, the difference between  $V_{CC}$  and  $V_{EE}$  is five volts. Therefore, using the configuration of Figure 21, a maximum analog signal of five volts peak—to—peak can be controlled. Unused analog inputs/outputs may be left floating (i.e., not connected). However, tying unused analog inputs and

outputs to  $V_{CC}$  or GND through a low value resistor helps minimize crosstalk and feedthrough noise that may be picked up by an unused switch.

Although used here, balanced supplies are not a requirement. The only constraints on the power supplies are that:

$$V_{EE}$$
 – GND = 0 to – 6 volts  
 $V_{CC}$  – GND = 2.5 to 6 volts  
 $V_{CC}$  –  $V_{EE}$  = 2.5 to 6 volts  
and  $V_{EE}$  ≤ GND

When voltage transients above  $V_{CC}$  and/or below  $V_{EE}$  are anticipated on the analog channels, external Germanium or Schottky diodes  $(D_x)$  are recommended as shown in Figure 22. These diodes should be able to absorb the maximum anticipated current surges during clipping.

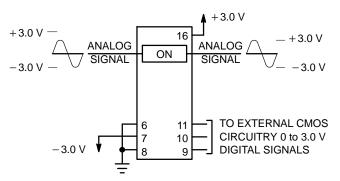


Figure 20. Application Example

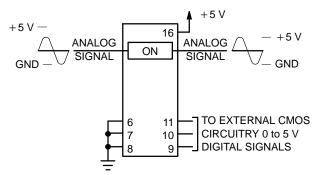


Figure 21. Application Example

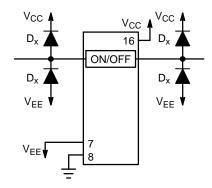


Figure 22. External Germanium or Schottky Clipping Diodes

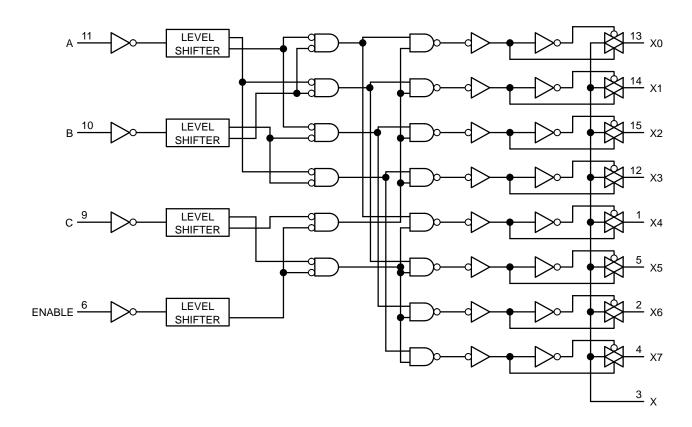
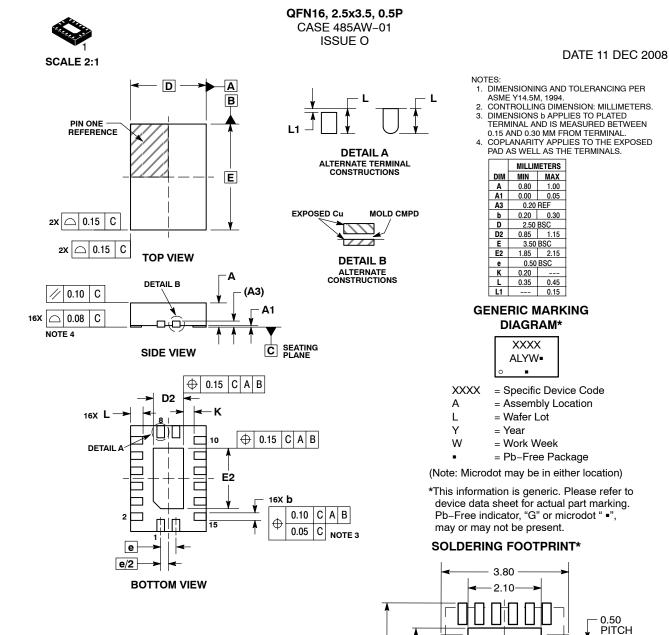


Figure 23. Function Diagram, LVX4051



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

16X

0.30

DIMENSIONS: MILLIMETERS

DESCRIPTION:	QFN16, 2.5X3.5, 0.5P		PAGE 1 OF 1
DOCUMENT NUMBER:	98AON36347E	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED of the controlled except when accessed directly from the controlled except when stamped "CONTROLLED of the controlled except when stamped	

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PACKAGE

## **MECHANICAL CASE OUTLINE**



**DATE 29 DEC 2006** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27 BSC		0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	COL DEDING	FOOTPRINT
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	3 FOOTPRINT
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		5.40 <del>→</del>
								7	,.40
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 <
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	T)		. 1	16
3.	DRAIN, #2	3.		3.	COMMON DRAIN (OUTPU			<b>↓ └──</b> ·	" 🗀
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	.,		<del>-</del> —	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPU	T)	16	5X <b>T</b>	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU		0.5	iii I	· —
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU		0.0	56	1
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	.,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	T)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPU				
13.	GATE, #2	13.	ANODE	13.	GATE N-CH	,			
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPU	T)			— VPITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU				<u>+-+</u> -
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH	•			
	*							<b>□</b> 8	9 + - + -
								<b>—</b> -	_ · · · · · · · · · · · · · · · · · · ·
									DIMENSIONS, MILLIMETERS
									DIMENSIONS: MILLIMETERS

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0.10 (0.004)

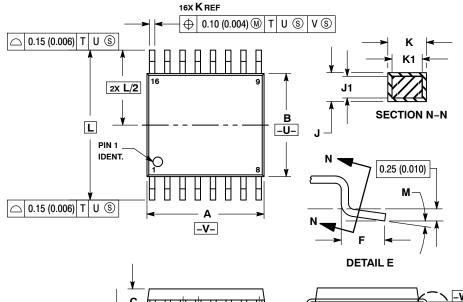
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

**DATE 19 OCT 2006** 



#### NOTES

- JIES:
  DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A DOES NOT INCLUDE MOLD
  FLASH. PROTRUSIONS OR GATE BURRS.
  MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026 BSC		
Н	0.18	0.28	0.007	0.011	
7	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
М	0°	8°	0 °	8°	

#### **SOLDERING FOOTPRINT**

G



## **GENERIC MARKING DIAGRAM\***

168888888 XXXX XXXX **ALYW** 1<del>88888888</del>

XXXX = Specific Device Code Α = Assembly Location = Wafer Lot L

Υ = Year W = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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